

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

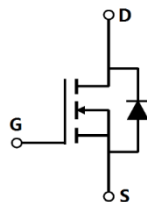
The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

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Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	700	V
$I_{D, pulse}$	6	A
$R_{DS(ON), max} @ V_{GS}=10V$	2.4	
Q_g	5.1	nC

Product Name	Package	Marking
OSG65R2K4AF	TO251	OSG65R2K4A



Absolute Maximum Ratings at $T_j=25$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25$ °C	I_D	2	A
Continuous drain current ¹⁾ , $T_C=100$ °C		1.25	
Pulsed drain current ²⁾ , $T_C=25$ °C	$I_{D, pulse}$	6	A
Continuous diode forward current ¹⁾ , $T_C=25$ °C	I_S	2	A
Diode pulsed current ²⁾ , $T_C=25$ °C	$I_{S, pulse}$	6	A
Power dissipation ³⁾ , $T_C=25$ °C	P_D	20	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	56	mJ
MOSFET dv/dt ruggedness, V_{DS}	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS}	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R	6.3	°C/W
Thermal resistance, junction-ambient ⁴⁾	R	62	°C/W

Electrical Characteristics at $T_j=25$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	$V_{GS}=0$ V, $I_D=250$ A
		700	770			$V_{GS}=0$ V, I_D , $T_j=150$ °C
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}$, $I_D=250$ A

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		118		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, Hz
Output capacitance	C_{oss}		12.5		pF	
Reverse transfer capacitance	C_{rss}		0.76		pF	
Turn-on delay time	$t_{d(on)}$		46.4		ns	$V_{GS}=10\text{ V}$, $V_{DS}=380\text{ V}$, $R_G=25$ $I_D=2\text{ A}$
Rise time	t_r		28.8		ns	
Turn-off delay time	$t_{d(off)}$		111.1		ns	
Fall time	t_f		48		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		5.7		nC	$V_{GS}=10\text{ V}$, $V_{DS}=480\text{ V}$, $I_D=2\text{ A}$
Gate-source charge	Q_{gs}		1.1		nC	
Gate-drain charge	Q_{gd}		2.5		nC	
Gate plateau voltage	$V_{plateau}$		5.4		V	

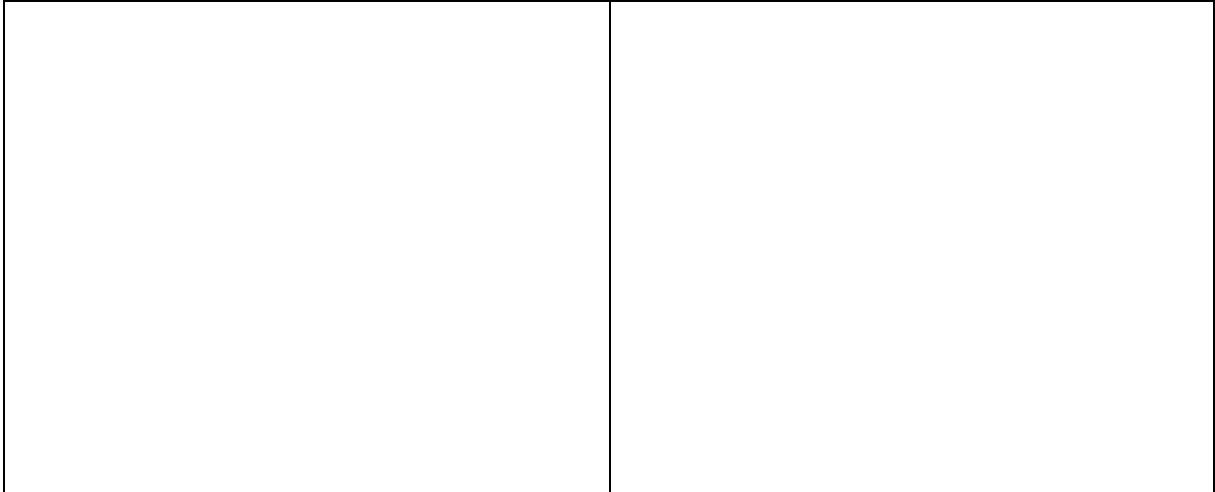
Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	$I_S=2\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		130		ns	$I_S=2\text{ A}$,
Reverse recovery charge	Q_{rr}		0.655		C	
Peak reverse recovery current	I_{rrm}		8.5		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of R_{θ} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $L=20\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams



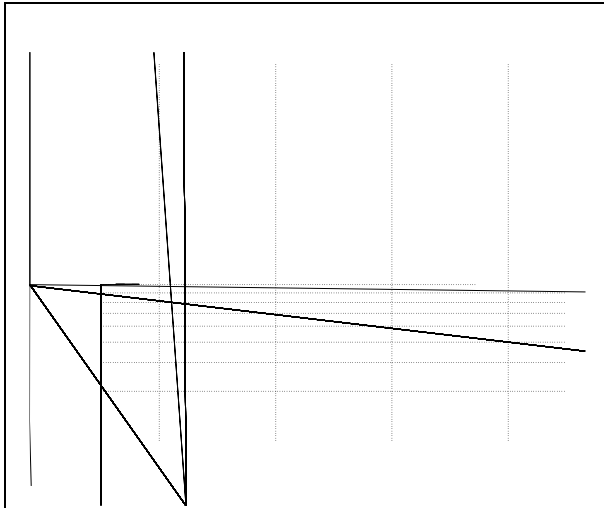


Figure 7. Forward characteristic of body diode

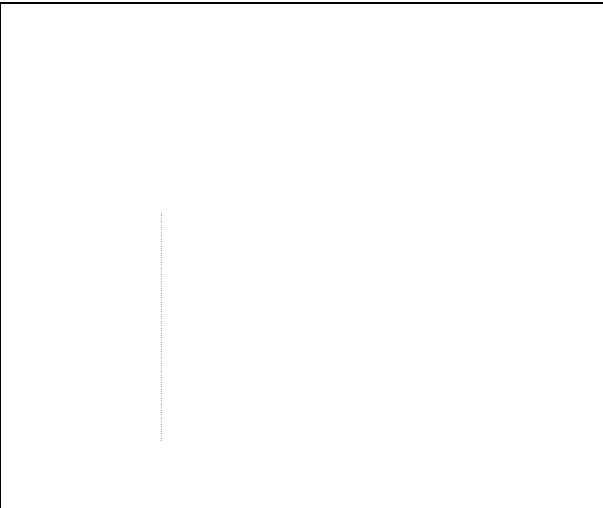


Figure 8. Drain-source on-state resistance

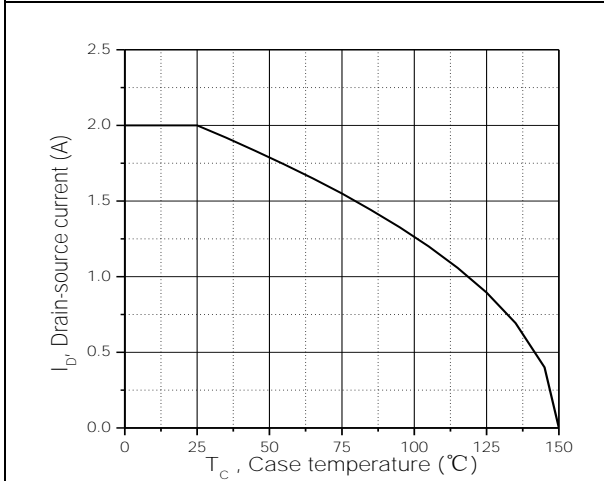


Figure 9. Drain current



Figure 10. Safe operation area T_C=25 °C

Test circuits and waveforms

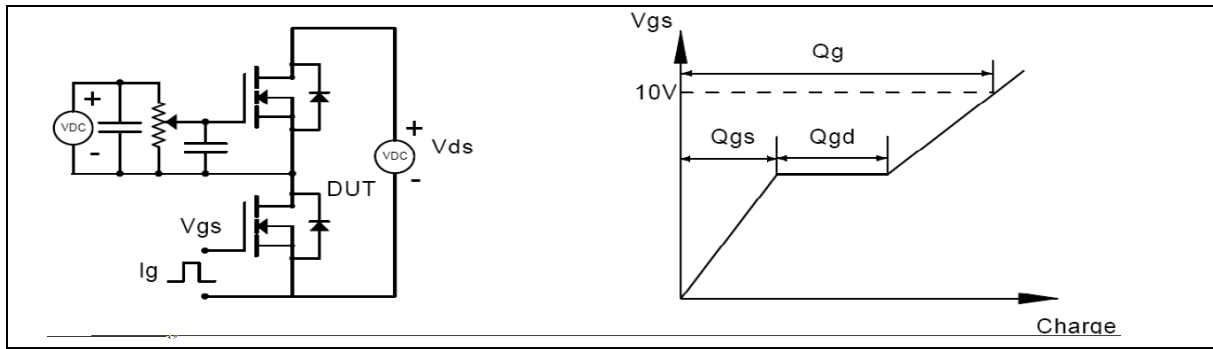


Figure 1. Gate charge test circuit & waveform

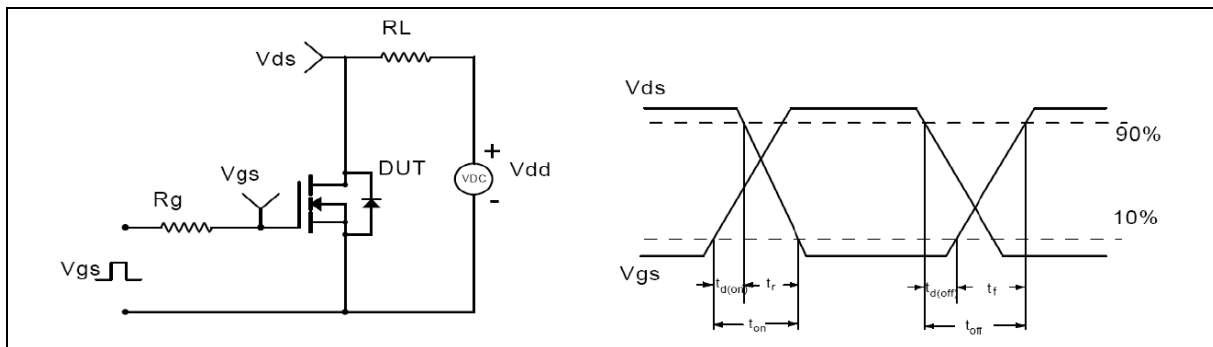


Figure 2. Switching time test circuit & waveforms

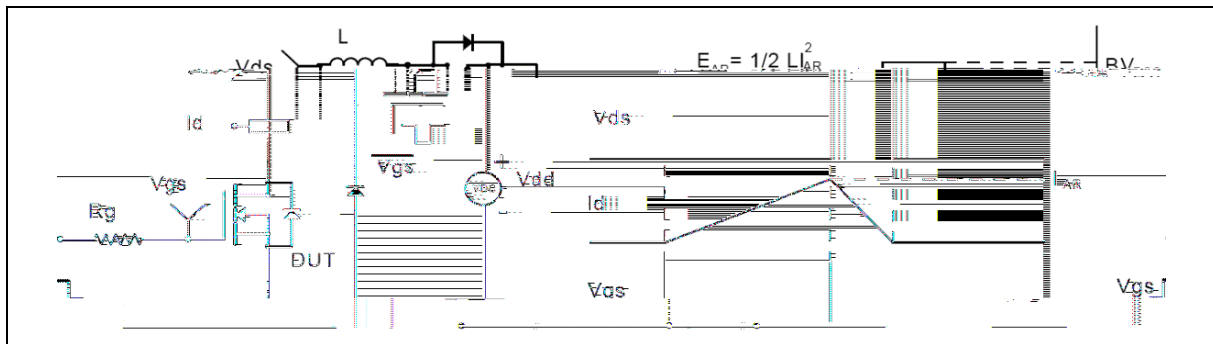


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

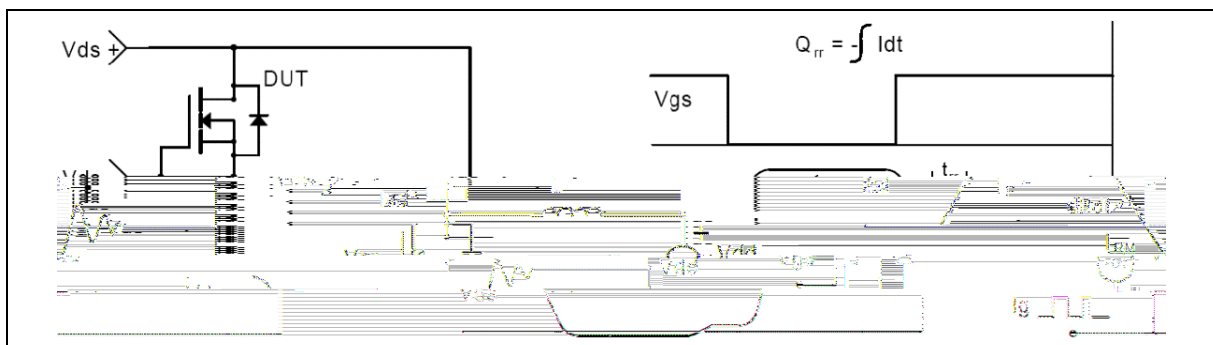


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information

Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
	0.00	0.04	0.10
b3	5.20	5.33	5.50
	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-

Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.35
A1	0.90	1.01	1.10
b	0.56	-	0.69
b1	0.55	0.60	0.65
b2	0.77	-	0.90
b3	0.76	0.81	0.86
b4	5.23	5.33	5.43
b5	-	-	1.05
c	0.46	-	0.59
c1	0.45	0.51	0.55
c2	0.46	-	0.59
D	6.00	6.10	6.20
D1	5.20	-	-
E	6.50	6.60	6.70
E1	4.60	4.83	5.00
e	2.24	2.29	2.34
e1	4.47	4.57	4.67
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.95	1.16	1.35
L2	0.90	1.08	1.25
	3°	5°	7°
	1°	3°	5°

Version2: TO251-J package outline dimension

OSG65R2K4AF
Enhancement Mode N-Channel Power MOSFET 